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# Analysis of spin-coherent drift-diffusion model for spin-polarized transport in semiconductors

Ansgar Jüngel\*, Claudia Negulescu, Polina Shpartko\* polina.shpartko@tuwien.ac.at

\* Institute of Analysis and Scientific Computing - Vienna University of Technology

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#### Main theses

- The model – continuity equations (for electron density components) + Poisson equation (for electric potential) – describes electron transport in semiconductor with magnetic properties

- Equations in the system are *strongly coupled*, system is *nonlinear* (coupling of the densities and potential)

- We present analytical results (existence, uniqueness of the solution, its boundedness, monotonicity of the entropy) and numerical results for 1D.

## Model

We studied a spin-coherent matrix drift-diffusion model derived in the work [1]:

$$\partial_{t}N + \operatorname{div}J + i\gamma[N, \vec{m} \cdot \vec{\sigma}] = \frac{1}{\tau} \left( \frac{1}{2} \operatorname{tr}(N) \sigma_{0} - N \right), \qquad (1)$$

$$J = -DP^{-1/2} (\nabla N + N \nabla V) P^{-1/2}, \qquad (2)$$

$$N = \frac{1}{2} n_{D} \sigma_{0} \quad \text{on } \partial\Omega, \ t > 0, \quad N(0) = N^{0} \quad \text{in } \Omega. \qquad (3)$$

$$(1)$$

$$\gamma > 0 \text{ - pseudo-exchange field,}$$

$$\vec{m} \in \mathbb{R}^{3} \text{ - direction of magnetization,}$$

$$\tau > 0 \text{ - spin-flip relaxation time,}$$

$$D = D(x) > 0 \text{ - space-dependent diffusion coefficient,}}$$

$$\vec{\sigma} = (\sigma_{1}, \sigma_{2}, \sigma_{2}) \text{ - triple of the Pauli matrices, } \sigma_{2} \text{ - upit matrices}}$$

 $N \in \mathbb{C}^{2 \times 2}$  - electron density,  $J \in \mathbb{C}^{2 \times 2}$  - current,  $\Omega \subset \mathbb{R}^3$  - domain, V - potential.

 $n = \frac{1}{2}n_D \sigma_0 \quad \text{on } \partial \Omega, \quad \nu > 0, \quad n(0) = N \quad \text{in } \Omega.$  $-\lambda_D^2 \Delta V = \operatorname{tr}(N) - C(x) \quad \text{in } \Omega, \quad V = V_D \quad \text{on } \partial \Omega.$ 

 $\vec{\sigma} = (\sigma_1, \sigma_2, \sigma_3)$  - triple of the Pauli matrices,  $\sigma_0$  - unit matrix in  $\mathbb{C}^{2 \times 2}$ ,  $P = \sigma_0 + p \vec{m} \cdot \vec{\sigma}$ , where  $p = p(x) \in [0, 1)$ .

The model describes evolution of electron charge and spin densities in semiconductor matter under impact of electric and magnetic fields.

It takes into account drift and diffusion of electron charge and spin densities, precession of spin around magnetic field direction, relaxation of spin.

Difficulties: strong coupling of the model equations and the quadratic-type nonlinearity of the drift term. Due to this there are no analytical results available for systems like this one.

Theory

Reformulation of the problem (1)-(4) in Pauli basis:  $N = \frac{1}{2}n_0\sigma_0 + \vec{n}\cdot\vec{\sigma}$ ,  $J = \frac{1}{2}j_0\sigma_0 + \vec{j}\cdot\vec{\sigma}$ .  $n_0$  - electron charge density,  $\vec{n} = (n_1, n_2, n_3)$  - spin-vector density.

$$\begin{split} \partial_t n_0 &- \operatorname{div} \left( \frac{D}{\eta^2} (J_0 - 2p \vec{J} \cdot \vec{m}) \right) = 0, \\ \partial_t n_k &- \operatorname{div} \left( \frac{D}{\eta^2} \Big( \eta J_k + (1 - \eta) (\vec{J} \cdot \vec{m}) m_k - \frac{p}{2} J_0 m_k \Big) \Big) - 2\gamma (\vec{n} \times \vec{m})_k = -\frac{n_k}{\tau}, \\ k &= 1, ..3, \ J_0 = \nabla n_0 + n_0 \nabla V, \ \vec{J} = \nabla \vec{n} + \vec{n} \nabla V, \ x \in \Omega, \ t > 0. \end{split}$$

Advantage: system of scalar equations

Main analytical result:

**Theorem 1** (Existence of bounded weak solutions). Let T > 0,  $\Omega \subset \mathbb{R}^3$  - bounded domain :  $\partial \Omega \in C^{1,1}$ . Let  $\lambda_D$ ,  $\gamma$ , D > 0,  $0 \le p < 1$ ,  $\vec{m} \in \mathbb{R}^3$  :  $|\vec{m}| = 1$ ,  $C \in L^{\infty}(\Omega)$ ,

$$0 \le n_D \in H^1(\Omega) \cap L^{\infty}(\Omega), \quad V_D \in W^{2,q_0}(\Omega), \quad q_0 > 3, \\ n_0^0, \, \vec{n}^0 \cdot \vec{m}, \, |\vec{n}^0| \in L^{\infty}(\Omega), \quad \frac{1}{2}n_0^0 \pm \vec{n}^0 \cdot \vec{m} \ge 0.$$

We considered 1D problem for 3-layered structure composed of layers of different magnetic and semiconductor properties:

Numerics



This is a "toy problem" which could be considered as a first approximation of *spin transistor*.

Then  $\exists$  a unique solution  $(N = \frac{1}{2}n_0\sigma_0 + \vec{n} \cdot \vec{\sigma}, V)$  to (1) - (4) such that

 $n_0, n_k \in W^{1,2}(0, T; H_0^1, L^2), \quad V \in L^{\infty}(0, \infty; W^{2,q_0}(\Omega)), \quad q_0 > 3, \\ 0 \le n_0 \pm \vec{n} \cdot \vec{m} \in L^{\infty}(0, \infty; L^{\infty}(\Omega)), \quad |\vec{n}| \in L^{\infty}(0, T; L^{\infty}(\Omega)).$ 

The **key idea** of the proof – exploiting of reformulations with different variables:

- in Pauli basis  $(n_0, n_1, n_2, n_3)$ 

- spin up/down densities:  $n_{\pm} = \frac{1}{2}n_0 \pm \vec{n} \cdot \vec{m}$ 

- parallel/perpendicular densities:  $\vec{n}_{\parallel} = (\vec{n} \cdot \vec{m})\vec{m}$  and  $\vec{n}_{\perp} = \vec{n} - (\vec{n} \cdot \vec{m})\vec{m}$ .

For existence proof we used Leray-Schauder Fixed Point Theorem, for boundedness estimates – Stampacchia and Moser-type iteration methods.

Von-Neumann entropy:

$$H_Q(t) = \int_{\Omega} \left( \operatorname{tr}[N(\log N - 1) - N_D(\log N_D - 1)] + \frac{\lambda_D^2}{2} |\nabla(V - V_D)|^2 \right) dx$$

**Proposition 2** (Monotonicity of  $H_Q$ ). Let  $\log(n_D/2) + V_D = \text{const.}$  in  $\Omega$ , (N, V) - a smooth solution to (1)-(4) :  $\frac{1}{2}n_0 > |\vec{n}|$  in  $\Omega$ ,  $t \ge 0$ . Then  $t \mapsto H_Q(t)$  is nonincreasing for t > 0.

This follows from spectral theory and matrix trace properties.

Entropy  $H_Q(t)$  of numerical solution converging to the thermal equilibrium state:



**Difficulties**: discontinuity of coefficients due to abrupt change of magnetic properties, **numerical degeneration** of Poisson equation (small  $\lambda_D^2$ ), possible instability due to large  $\nabla V$ .

Solution was implemented with finite volumes method, implicit in time; *Gummel iteration scheme* was used for mutual solution of continuity and Poisson equations.

Solution of continuity equations with given (linear) potential was exploited as a *reference solution* as it was already presented in the work [1].

Influence of potential nonlinearity is significant, especially for smaller spin polarization p:



Figure 3: Charge density  $n_0$ : solution of continuity equations with given (linear) potential (left), solution of full drift-diffusion-Poisson model (right).

On the contrary solution with Poisson equation for  $n_3$  differs from solution with linear potential only slightly:



Figure 1: Semilogarithmic plot of the entropy  $H_Q(t)$ : exponential decay

### **Future work**

-Solution in 2D

-Coupling with Landau-Lifschits-Gilbert equation (gives evolution of  $\vec{m}$  in time)

#### References

Figure 4: Charge density  $n_3$ : solution of continuity equations with given (linear) potential (left), solution of full drift-diffusion-Poisson model (right).

**Conclusion:** Implemented numerics gives distribution of charge and spin densities, respectively charge and spin currents, but for now only in 1D.

[1] S. Possanner and C. Negulescu. Diffusion limit of a generalized matrix Boltzmann equation for spin-polarized transport. Kinetic Related Models 4 (2011), 1159-1191.